

RM1200HE-66S

HIGH POWER SWITCHING USE
INSULATED TYPE

High Voltage Diode Module

RM1200HE-66S



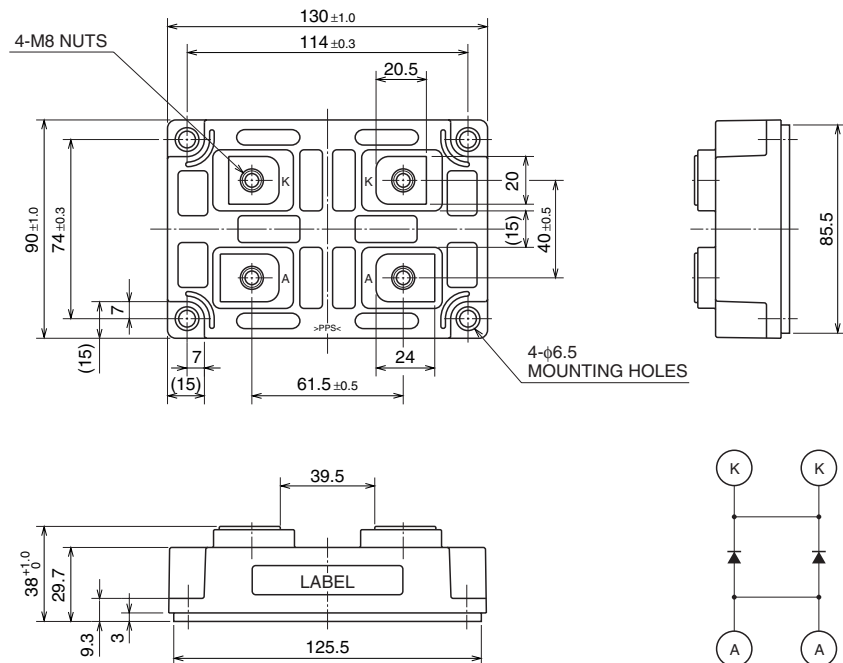
- IF 1200A
- VRRM 3300V
- Insulated Type
- 1-element in a Pack
- AISiC Baseplate

APPLICATION

Traction drives, High Reliability Converters / Inverters, DC choppers

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



CIRCUIT DIAGRAM

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May 2009

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MAXIMUM RATINGS

Symbol	Item	Conditions	Ratings	Unit
VRRM	Repetitive peak reverse voltage	T _j = 25 °C	3300	V
VRSM	Non-repetitive peak reverse voltage	T _j = 25 °C	3300	V
VR(DC)	Reverse DC voltage	T _j = 25 °C	2200	V
I _F	DC forward current	T _c = 25 °C	1200	A
I _{FSM}	Surge forward current	T _j = 25 °C start, t _w = 8.3 ms Half sign wave	9600	A
I ² t	Current-squared, time integration	T _j = 25 °C start, t _w = 8.3 ms Half sign wave	384	kA ² s
V _{iso}	Isolation voltage	Charged part to the baseplate RMS sinusoidal, 60Hz 1min.	6000	V
T _j	Junction temperature	—	−40 ~ +150	°C
T _{op}	Operating temperature	—	−40 ~ +125	°C
T _{stg}	Storage temperature	—	−40 ~ +125	°C

ELECTRICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min	Typ	Max	
IRRM	Repetitive reverse current	V _{RM} = VRRM	T _j = 25 °C	—	5	mA
			T _j = 125 °C	—	30	
V _{FM}	Forward voltage (Note 1)	I _F = 1200 A	T _j = 25 °C	—	3.20	V
			T _j = 125 °C	—	3.10	
t _{rr}	Reverse recovery time	V _R = 1650 V, I _F = 1200 A di/dt = −3500 A/μs L _s = 100nH, T _j = 125 °C	—	—	1.4	μs
I _{rr}	Reverse recovery current		—	1400	—	A
Q _{rr}	Reverse recovery charge		—	900	—	μC
E _{rec}	Reverse recovery energy (Note 2)		—	0.85	—	J/P

Note 1. It doesn't include the voltage drop by internal lead resistance.

2. E_{rec} is the integral of 0.1V_R × 0.1I_{rr} × dt.

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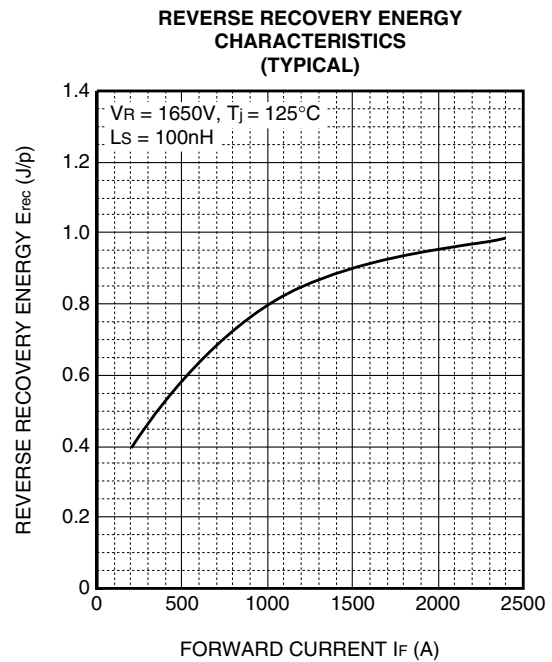
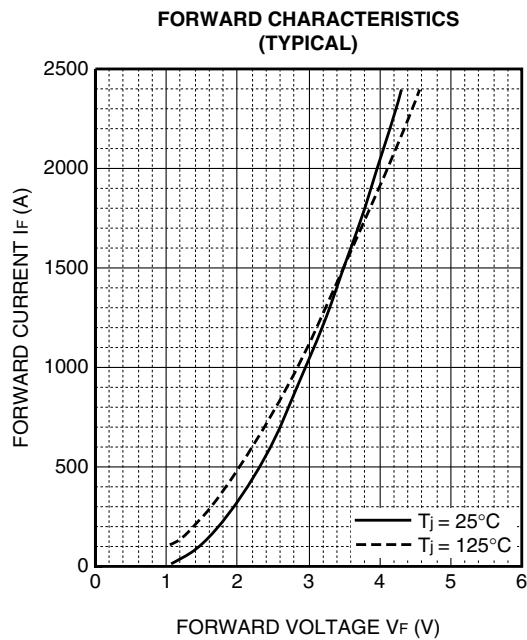
THERMAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min	Typ	Max	
$R_{th(j-c)}$	Thermal resistance	Junction to case	—	—	20.0	K/kW
$R_{th(c-f)}$	Contact thermal resistance	Case to Fin, $\lambda_{grease} = 1W/m \cdot K$ $D(c-f) = 100\mu m$	—	15.0	—	K/kW

MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min	Typ	Max	
M_t	Mounting torque	M8: Main terminals screw	6.67	—	13.0	N·m
M_s		M6: Mounting screw	2.84	—	6.0	N·m
m	Mass	—	—	0.66	—	kg

PERFORMANCE CURVES

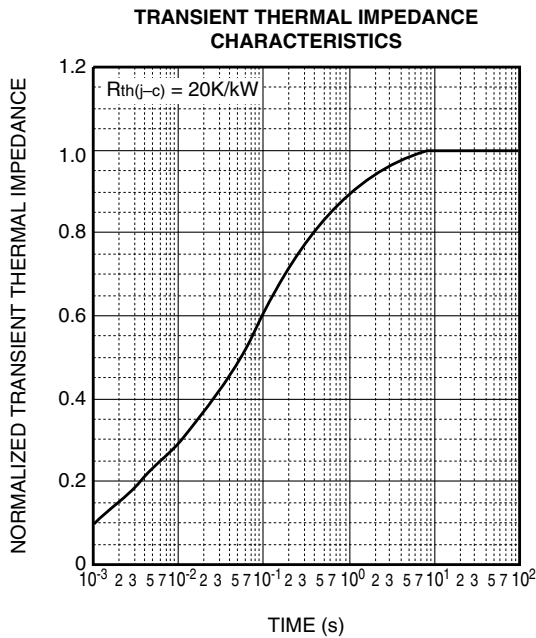
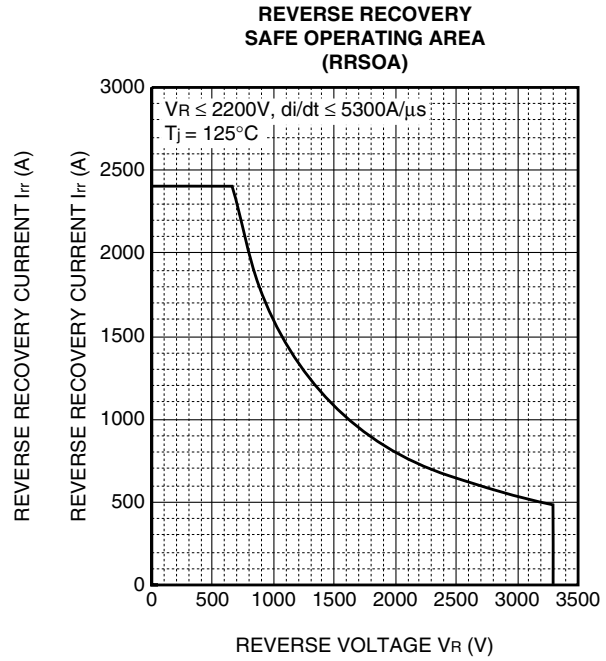
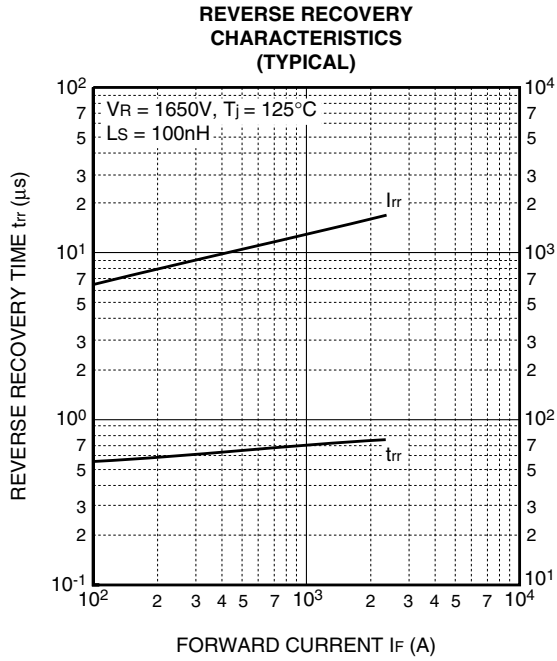


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